






10/724/41

<b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)				ATTY DOCKET NO. <b>INF-119</b>		SERIAL NO. <b>New Application</b>		
				GRIT SCHWALBE ET AL.				
				FILING <b>DECEMBER 1, 2003</b>		GROUP <b>Unknown 2813</b>		
<b>U.S. PATENT DOCUMENTS</b>								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
		5,660,681	08/26/97	FUKUDA ET AL.	438	695	08/19/96	
		6,232,237	05/15/01	TAMAOKA ET AL.	438	725	12/08/98	
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		2002/0164877	11/07/02	CATABAY ET AL.	438	694	05/02/01	
<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
		Article entitled "Limitation of HF-Based Chemistry for Deep-Submicron Contact Hole Cleaning on Silicides" by M.R. Baklanov et al., J. Electrochem. Soc., Vol. 145, No. 9 September 1998 by The Electrochemical Society, Inc., pp 3240-3246.						
		Article entitled "low-k dielectric etching" by D.J. Thomas et al., published March 2001 in Solid State Technology, pages 107, 108, 112-116 (www.solid-state.com)						
		Copy of German Office Action dated October 20, 2003						
EXAMINER 				DATE CONSIDERED <b>9/24/03</b>				
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								